## Amendments to the Specification:

## Please rewrite the paragraph on page 1, lines 5-9 as follows:

## CROSS REFERENCE TO RELATED APPLICATION

This application is a division of U.S. Application Serial No. 10/197,037, filed July 17, 2002, now U.S. Patent No. 6,641,941, and also claims the benefit of Japanese Patent Application No. P2001-219,092 filed July 19, 2001 and Japanese Application No. P2002-180,769 filed June 21, 2002, the entireties of which are incorporated by reference.

## Please rewrite paragraph [0087] as follows:

[0087] The crystalline phases in each film were identified using an X-ray diffraction system, according to the conditions below. The YAL(420)/YAG(420) ratio was then calculated:

CuK $\alpha$ , 50 kV, 300 mA, 2  $\theta$  = 20 to 70 °;

Applied system: Rotating anode type X-ray diffraction system "RINT" supplied by "Rigaku Denki."